BGA2866

MMIC wideband amplifier

Rev. 4 — 13 July 2015

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Input internally matched to 50 Ω
- A gain of 23.2 dB at 250 MHz increasing to 24.3 dB at 2150 MHz
- Output power at 1 dB gain compression = 4 dBm
- Supply current = 17.4 mA at a supply voltage of 5 V
- Reverse isolation > 32 dB up to 2150 MHz
- Good linearity with low second order and third order products
- Noise figure = 3.8 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	V _{CC}		
2, 5	GND2	654	
3	RF_OUT		6-
4	GND1	0	4 2, 5
6	RF_IN	□1 □2 □3	h h
			sym052



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3. Ordering information

Table 2. Ordering information

Type number	Package						
	Name	Description	Version				
BGA2866	-	plastic surface-mounted package; 6 leads	SOT363				

4. Marking

Table 3. Marking

Type number	Marking code	Description
BGA2866	*ED	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	-0.5	+7.0	V
Icc	supply current		-	36	mA
P _{tot}	total power dissipation	T _{sp} = 90 °C	-	200	mW
T _{stg}	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P _{drive}	drive power		-	+10	dBm

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	$P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$	300	K/W

7. Characteristics

Table 6. Characteristics

 $V_{CC} = 5.0 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -40 \text{ dBm}; T_{amb} = 25 \text{ °C}; measured on demo board; unless otherwise specified.}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		4.5	5.0	5.5	V
I _{CC}	supply current		14.7	17.4	20.1	mΑ

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 Table 6.
 Characteristics ...continued

 $V_{CC} = 5.0 \text{ V; } Z_S = Z_L = 50 \Omega; P_i = -40 \text{ dBm; } T_{amb} = 25 \text{ °C; measured on demo board; unless otherwise specified.}$

$ \begin{array}{c} & f = 950 \text{ MHz} \\ \hline f = 2150 \text{ MHz} \\ \hline f = 2150 \text{ MHz} \\ \hline \end{array} \begin{array}{c} 23.2 2 \\ \hline f = 2150 \text{ MHz} \\ \hline \end{array} \begin{array}{c} 22.8 2 \\ \hline \end{array} \begin{array}{c} 2 \\ \hline \end{array} $	23.9 24.3 20	23.8 24.6	dB
$ \begin{array}{c} {\sf F} = 2150 {\sf MHz} & 22.8 \ 2 \\ {\sf RL_{in}} & {\sf input return loss} & {\sf f} = 250 {\sf MHz} & 18 \ 2 \\ {\sf f} = 950 {\sf MHz} & 24 \ 2 \\ {\sf f} = 2150 {\sf MHz} & 11 \ 1 \\ {\sf RL_{out}} & {\sf output return loss} & {\sf f} = 250 {\sf MHz} & 21 \ 2 \\ {\sf f} = 950 {\sf MHz} & 12 \ 1 \\ {\sf f} = 950 {\sf MHz} & 12 \ 1 \\ {\sf f} = 2150 {\sf MHz} & 10 \ 1 \\ {\sf ISL} & {\sf isolation} & {\sf f} = 250 {\sf MHz} & 40 \ 6 \\ {\sf f} = 950 {\sf MHz} & 41 \ 4 \\ {\sf f} = 2150 {\sf MHz} & 32 \ 3 \\ {\sf NF} & {\sf noise figure} & {\sf f} = 250 {\sf MHz} & 3.4 \ 3 \\ {\sf f} = 950 {\sf MHz} & 3.4 \ 3 \\ {\sf f} = 950 {\sf MHz} & 3.4 \ 3 \\ {\sf f} = 2150 {\sf MHz} & 3.5 \ 3 \\ {\sf SL_{3dB}} & -3 {\sf dB \ bandwidth} & 3 {\sf dB \ below \ gain \ at 1 \ GHz} & 3.1 \ 3 \\ {\sf K} & {\sf Rollett \ stability \ factor} & {\sf f} = 250 {\sf MHz} & 3.3 \ 3 \\ {\sf dSl \ below \ gain \ at 1 \ GHz} & 3.3 \ 3 \\ {\sf dSl \ below \ gain \ at 1 \ GHz} & 3.3 \ 3 \\ {\sf dSl \ below \ gain \ at 1 \ GHz} & 3.3 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 1 \ GHz} & 3.3 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ below \ gain \ at 2 \ GHz} & 3.1 \ 3 \\ {\sf dSl \ dS$	24.3 20	24.6	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	20		dB
$ \begin{array}{c} $		25.8	dB
$ \begin{array}{c} $		22	dB
$ \begin{array}{c} {\sf RL}_{\sf out} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	26	28	dB
	18	24	dB
$ \begin{array}{c} \text{ISL} & \text{isolation} & \begin{array}{c} f = 2150 \text{MHz} \\ \end{array} & \begin{array}{c} 10 & 1 \\ \end{array} & \begin{array}{c} 1 \\ \end{array} & \begin{array}{c} 6 \\ \end{array} & \begin{array}{c} 1 \\ \end{array} & \begin{array}{c}$	26	30	dB
$ \begin{array}{c} \text{ISL} & \text{isolation} & \begin{array}{c} \text{f} = 250 \text{ MHz} \\ \hline \text{f} = 950 \text{ MHz} \\ \hline \text{f} = 2150 \text{ MHz} \\ \end{array} & \begin{array}{c} \text{41} & \text{44} \\ \text{f} = 2150 \text{ MHz} \\ \end{array} & \begin{array}{c} \text{32} & \text{33} \\ \end{array} \\ \text{NF} & \begin{array}{c} \text{noise figure} \\ \hline \text{f} = 250 \text{ MHz} \\ \hline \text{f} = 950 \text{ MHz} \\ \hline \text{f} = 2150 \text{ MHz} \\ \end{array} & \begin{array}{c} \text{3.4} & \text{3} \\ \text{3.6} & \text{3.5} \\ \end{array} & \begin{array}{c} \text{3.6} \\ \text{3.6} \\ \end{array} & \begin{array}{c} \text{3.7} \\ \text{3.6} \\ \end{array} & \begin{array}{c} \text{3.7} \\ \text{3.8} \\ \end{array} & \begin{array}{c} $	13	14	dB
	11	14	dB
	60	81	dB
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	43	44	dB
	35	37	dB
$f = 2150 \text{ MHz} \qquad \qquad 3.5 \qquad 3$ $B_{-3dB} \qquad -3 \text{ dB bandwidth} \qquad \qquad 3 \text{ dB below gain at 1 GHz} \qquad \qquad 3.1 \qquad 3$ $K \qquad \text{Rollett stability factor} \qquad \qquad f = 250 \text{ MHz} \qquad \qquad 33 \qquad 3$	3.9	4.4	dB
B_{-3dB} -3 dB bandwidth 3 dB below gain at 1 GHz 3.1 3 K Rollett stability factor $f = 250$ MHz 33	3.8	4.2	dB
K Rollett stability factor f = 250 MHz 33 3	3.9	4.3	dB
	3.3	3.4	GHz
f = 950 MHz 3.8 4	35	37	
	4.1	4.4	
f = 2150 MHz 1.3 1	1.6	1.9	
$P_{L(sat)}$ saturated output power $f = 250 \text{ MHz}$ 5	6	7	dBm
	7	8	dBm
f = 2150 MHz 2 4	4	5	dBm
$P_{L(1dB)}$ output power at 1 dB gain compression $f = 250 \text{ MHz}$ 3 4	4	5	dBm
	4	5	dBm
f = 2150 MHz 1 3	3	4	dBm
$IP3_I$ input third-order intercept point $P_{drive} = -36 \text{ dBm (for each tone)}$			
$f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ -6 -	-4	-2	dBm
$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ -9 -9	-7	-4	dBm
$f_1 = 2150 \text{ MHz}; f_2 = 2151 \text{ MHz}$ -16 -	-12	-9	dBm
IP3 _O output third-order intercept point $P_{drive} = -36 \text{ dBm (for each tone)}$			
$f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ 17 1	19	21	dBm
$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ 15 1	17	20	dBm
$f_1 = 2150 \text{ MHz}; f_2 = 2151 \text{ MHz}$ 9 1	12	15	dBm
$P_{L(2H)}$ second harmonic output power $P_{drive} = -33 \text{ dBm}$			
	-51	-49	dBm
$f_{1H} = 950 \text{ MHz}; f_{2H} = 1900 \text{ MHz}$ -43 -	-41	-40	dBm
$\Delta IM2$ second-order intermodulation distance $P_{drive} = -36 \text{ dBm (for each tone)}$			
$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ 32 4	47	58	dBc

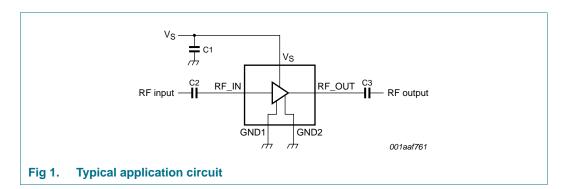
MMIC wideband amplifier

8. Application information

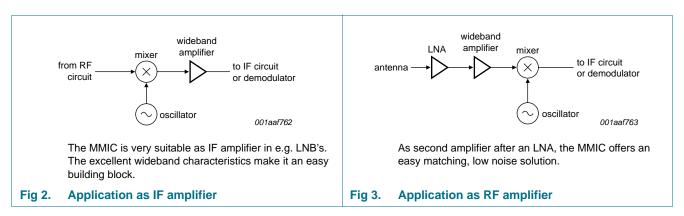
<u>Figure 1</u> shows a typical application circuit for the BGA2866 MMIC. The device is internally matched to $50~\Omega$ and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



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8.2 Graphs

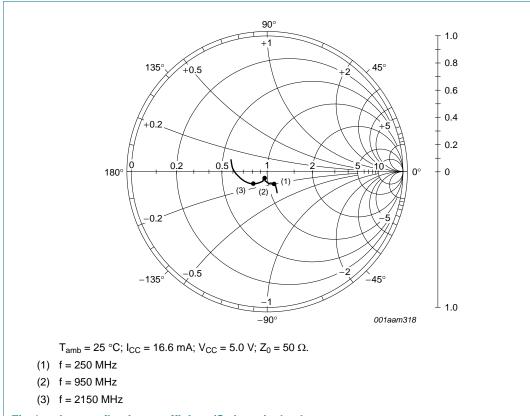
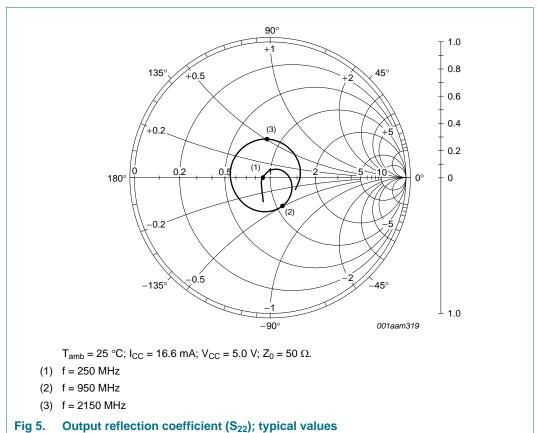
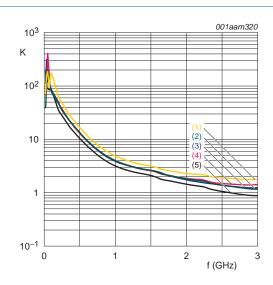


Fig 4. Input reflection coefficient (S₁₁); typical values

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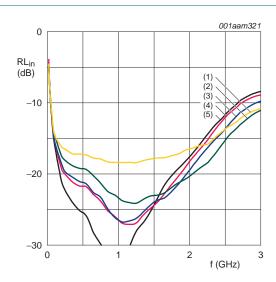
MMIC wideband amplifier



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 6. Rollett stability factor as function of frequency; typical values

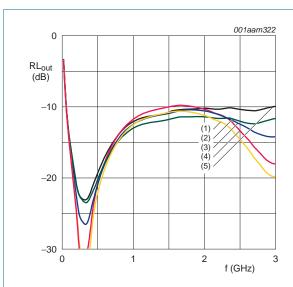


 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 7. Input return loss as function of frequency; typical values

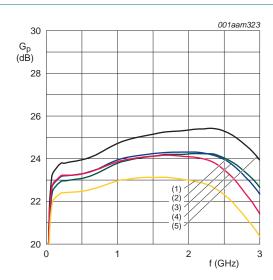
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 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 8. Output return loss as function of frequency; typical values



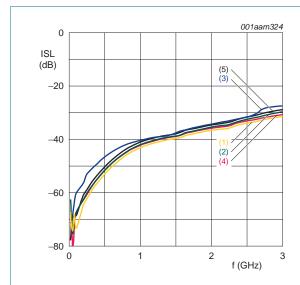
 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 9. Power gain as function of frequency; typical values

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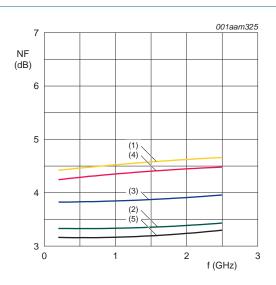
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 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 10. Isolation as function of frequency; typical values



 $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 14.36 \,\text{mA}$
- (2) $V_{CC} = 4.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.41 \,\text{mA}$
- (3) $V_{CC} = 5.0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 16.63 \,\text{mA}$
- (4) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 17.27 \,\text{mA}$
- (5) $V_{CC} = 5.5 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 19.29 \,\text{mA}$

Fig 11. Noise figure as function of frequency; typical values

8.3 Tables

Table 7. Supply current over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T _{amb} (°0	T _{amb} (°C)			
			-40	+25	+85		
Icc	supply current	V _{CC} = 4.5 V	16.41	15.27	14.36	mA	
		$V_{CC} = 5.0 \text{ V}$	17.73	16.63	15.85	mA	
	$V_{CC} = 5.5 \text{ V}$	19.29	17.73	17.27	mA		

Table 8. Second harmonic output power over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)		Unit	
			-40	+25	+85	
P _{L(2H)}	second harmonic output power	$f = 250 \text{ MHz}; P_{drive} = -33 \text{ dBm}$				
		V _{CC} = 4.5 V	-48	-49	-51	dBm
		V _{CC} = 5.0 V	-49	-51	-53	dBm
		V _{CC} = 5.5 V	-50	-52	-54	dBm
		$f = 950 \text{ MHz}; P_{drive} = -33 \text{ dBm}$				
		V _{CC} = 4.5 V	-40	-41	-42	dBm
		V _{CC} = 5.0 V	-40	-41	-42	dBm
		V _{CC} = 5.5 V	-40	-41	-42	dBm

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Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol	Parameter Conditions T _{amb} (°C)			Unit		
			-40	+25	+85	
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 4.5 V	-18	-18	-19	dBm
		V _{CC} = 5.0 V	-18	-18	-18	dBm
		V _{CC} = 5.5 V	-17	-18	-18	dBm
		f = 950 MHz				
		V _{CC} = 4.5 V	-19	-19	-19	dBm
		V _{CC} = 5.0 V	-18	-18	-19	dBm
		$V_{CC} = 5.5 \text{ V}$	-18	-18	-18	dBm
		f = 2150 MHz				
		$V_{CC} = 4.5 \text{ V}$	-20	-21	-22	dBm
		V _{CC} = 5.0 V	-20	-21	-22	dBm
		V _{CC} = 5.5 V	-20	-21	-22	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)		Unit	
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 4.5 V	4	3	3	dBm
		V _{CC} = 5.0 V	5	4	4	dBm
		V _{CC} = 5.5 V	5	5	4	dBm
		f = 950 MHz				
		V _{CC} = 4.5 V	4	3	3	dBm
		V _{CC} = 5.0 V	5	4	4	dBm
		V _{CC} = 5.5 V	6	5	4	dBm
		f = 2150 MHz				
		V _{CC} = 4.5 V	3	2	0	dBm
		V _{CC} = 5.0 V	4	2	1	dBm
		V _{CC} = 5.5 V	4	3	1	dBm

Table 11. Saturated output power over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		V _{CC} = 4.5 V	6	5	5	dBm
		V _{CC} = 5.0 V	7	6	6	dBm
		V _{CC} = 5.5 V	8	7	6	dBm
		f = 950 MHz				
		V _{CC} = 4.5 V	6	5	5	dBm
		V _{CC} = 5.0 V	7	7	5	dBm
		V _{CC} = 5.5 V	8	7	6	dBm
		f = 2150 MHz				
		V _{CC} = 4.5 V	4	3	2	dBm
		V _{CC} = 5.0 V	5	4	2	dBm
		V _{CC} = 5.5 V	5	4	2	dBm

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
ΔΙΜ2	second-order intermodulation distance	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 4.5 V	40	42	46	dBc
		V _{CC} = 5.0 V	44	47	51	dBc
		V _{CC} = 5.5 V	48	51	56	dBc
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 4.5 V	38	40	43	dBc
		V _{CC} = 5.0 V	42	43	45	dBc
		V _{CC} = 5.5 V	45	46	46	dBc

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	+25	+85	
IP3 _O	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 4.5 V	18	18	17	dBm
		V _{CC} = 5.0 V	20	19	18	dBm
		V _{CC} = 5.5 V	21	19	19	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 4.5 V	17	16	15	dBm
		V _{CC} = 5.0 V	18	17	16	dBm
		V _{CC} = 5.5 V	20	18	16	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$				
		V _{CC} = 4.5 V	13	11	9	dBm
		V _{CC} = 5.0 V	14	12	9	dBm
		V _{CC} = 5.5 V	15	12	10	dBm

Table 14. -3 dB bandwidth over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
B _{-3dB}	-3 dB bandwidth	V _{CC} = 4.5 V	3.375	3.245	3.059	GHz
		V _{CC} = 5.0 V	3.399	3.265	3.069	GHz
		V _{CC} = 5.5 V	3.416	3.278	3.078	GHz

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9. Test information

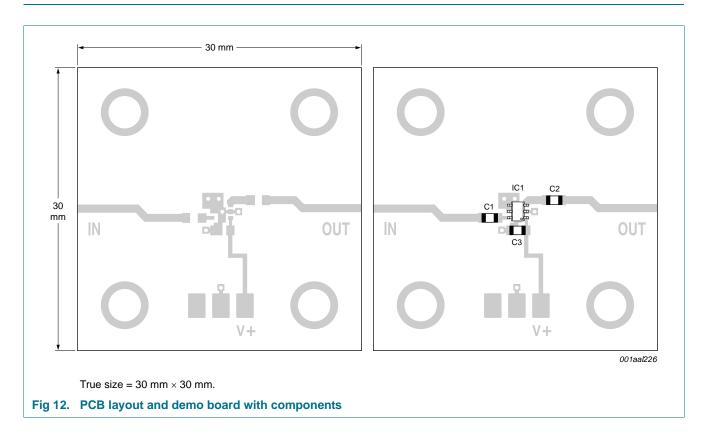


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions
C1, C2	multilayer ceramic chip capacitor	100 pF	0603
C3	multilayer ceramic chip capacitor	22 nF	0603
IC1	BGA2866 MMIC	-	SOT363

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10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

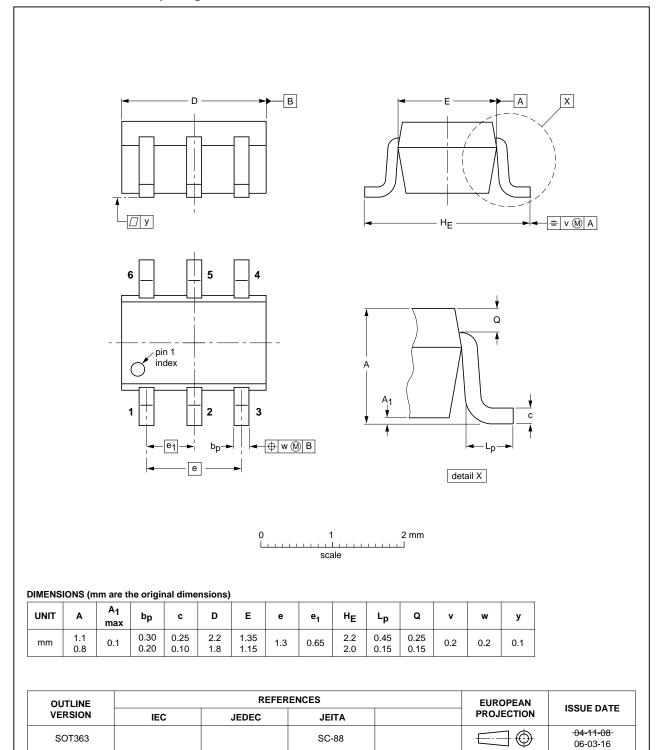


Fig 13. Package outline SOT363

RGA2866

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11. Abbreviations

Table 16. Abbreviations

Acronym	Description
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board
SMD	Surface Mounted Device

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGA2866 v.4	20150713	Product data sheet	-	BGA2866 v.3	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 				
BGA2866 v.3	20130827	Product data sheet	-	BGA2866 v.2	
BGA2866 v.2	20101101	Product data sheet	-	BGA2866 v.1	
BGA2866 v.1	20100817	Product data sheet	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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